



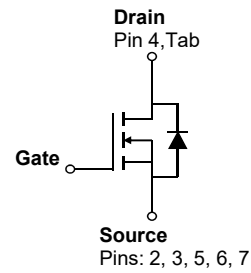
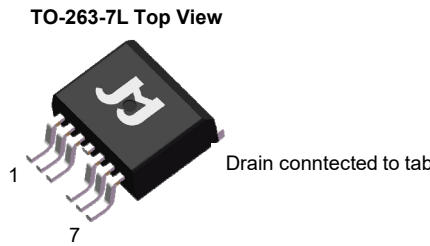
100V 1.6mΩ N-Ch Power MOSFET

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge, Q_g
- 100% UIS and R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant
- AEC-Q101 Qualified for Automotive Applications

Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th_Typ)}$	2.8	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	350	A
$R_{DS(ON)_Typ}$ (@ $V_{GS} = 10V$)	1.6	mΩ

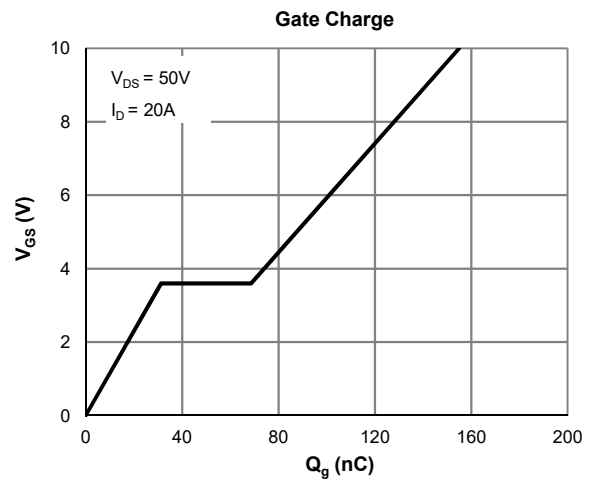
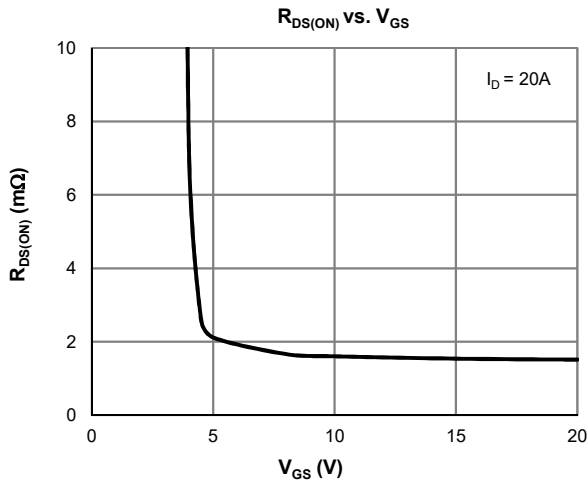


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1001AE7Q-13	TO-263-7L	7	SH1001A	1	-55 to 175	13-inch Reel	800

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	350
		$T_C = 100^\circ C$	247
Pulsed Drain Current ⁽²⁾	I_{DM}	1398	A
Avalanche Energy ⁽³⁾	E_{AS}	512	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	500
		$T_C = 100^\circ C$	250
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$			1.0	μA
			$T_J = 55^\circ\text{C}$		5.0	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.2	2.8	3.4	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		1.6	2.0	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		86		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.67	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			500	A

DYNAMIC PARAMETERS ⁽⁶⁾

Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		9623		pF
Output Capacitance	C_{oss}			2091		pF
Reverse Transfer Capacitance	C_{rss}			1.2		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.4		Ω

SWITCHING PARAMETERS ⁽⁶⁾

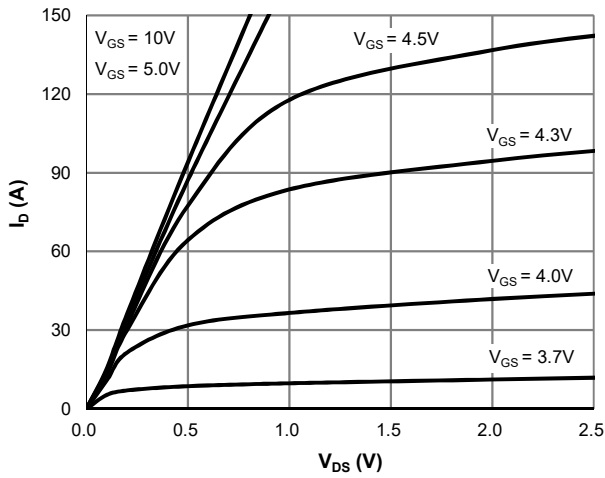
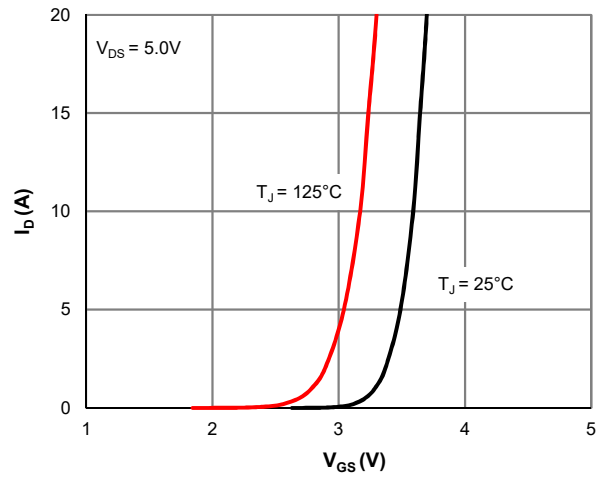
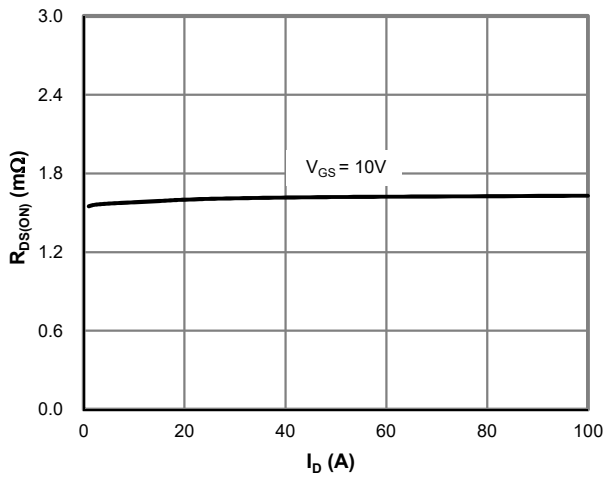
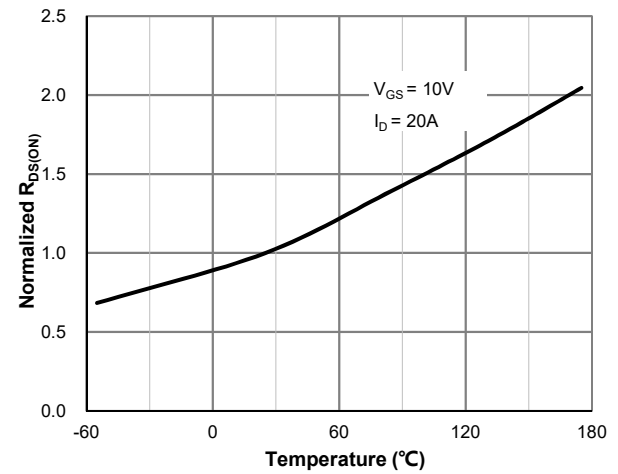
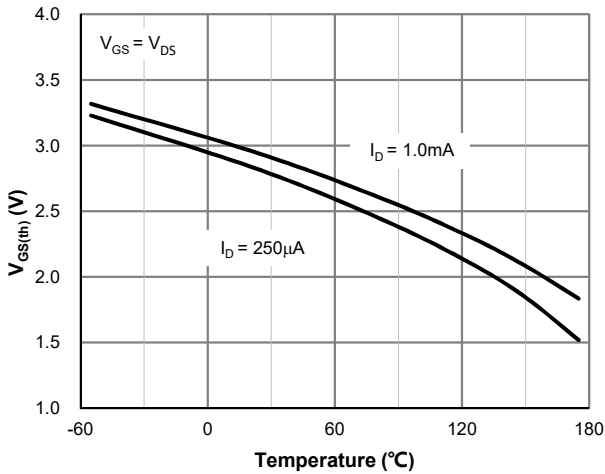
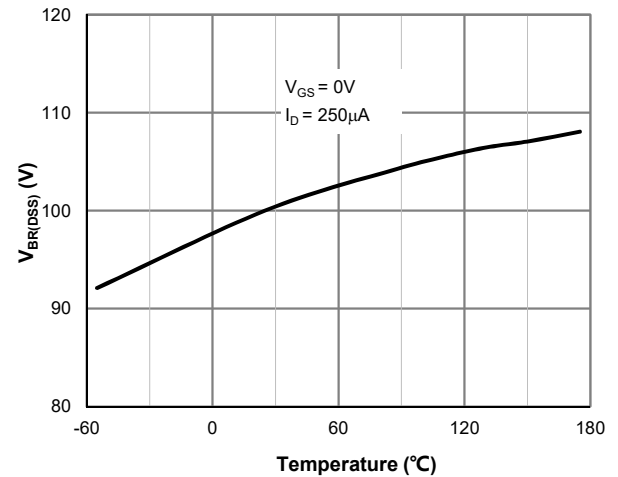
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$		155		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			101		nC
Gate Source Charge	Q_{gs}			31		nC
Gate Drain Charge	Q_{gd}			37		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 2.5\Omega, R_{GEN} = 6\Omega$		34		ns
Turn-On Rise Time	t_r			67		ns
Turn-Off DelayTime	$t_{D(off)}$			145		ns
Turn-Off Fall Time	t_f			111		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		76	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		116		nC

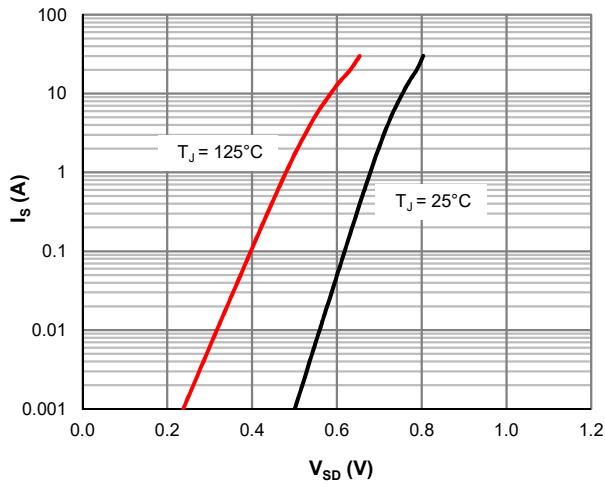
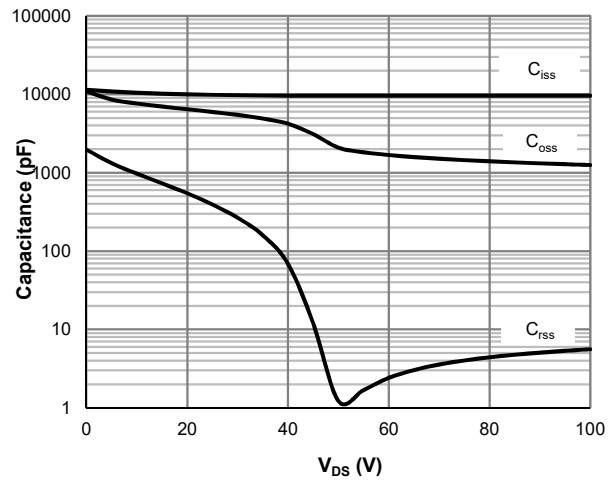
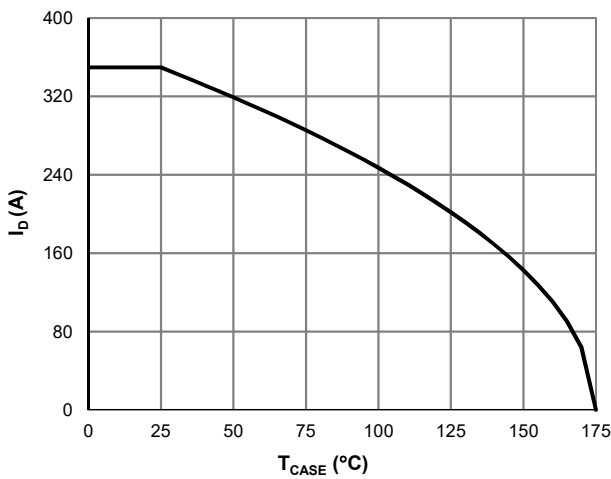
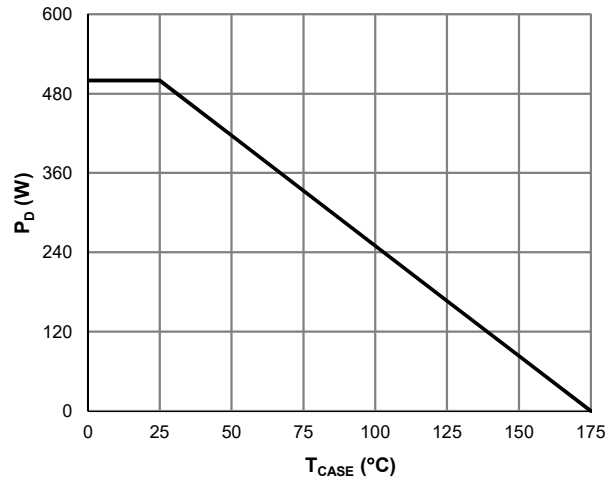
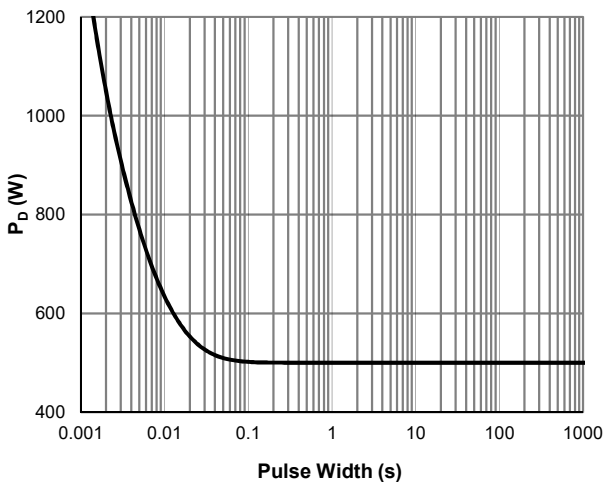
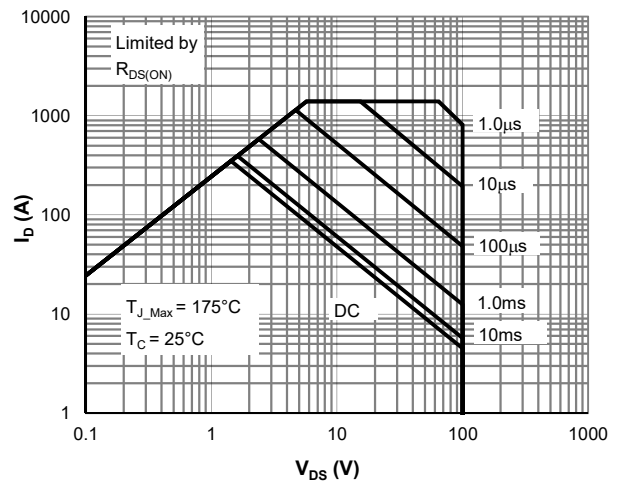
Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	49	59	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.30	0.40	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 175^\circ\text{C}$.
3. E_{AS} of 512 mJ is based on starting $T_J = 25^\circ\text{C}, L = 1.0\text{mH}, I_{AS} = 32\text{A}, V_{GS} = 10\text{V}, V_{DD} = 50\text{V}; 100\%$ test at $L = 0.3\text{mH}, I_{AS} = 81\text{A}$.
4. The power dissipation P_D is based on $T_{J_Max} = 175^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: $V_{GS(th)}$ vs. Junction Temperature

Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

Figure 7: Body-Diode Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Current De-rating

Figure 10: Power De-rating

Figure 11: Single Pulse Power Rating, Junction-to-Case

Figure 12: Maximum Safe Operating Area



Typical Electrical & Thermal Characteristics

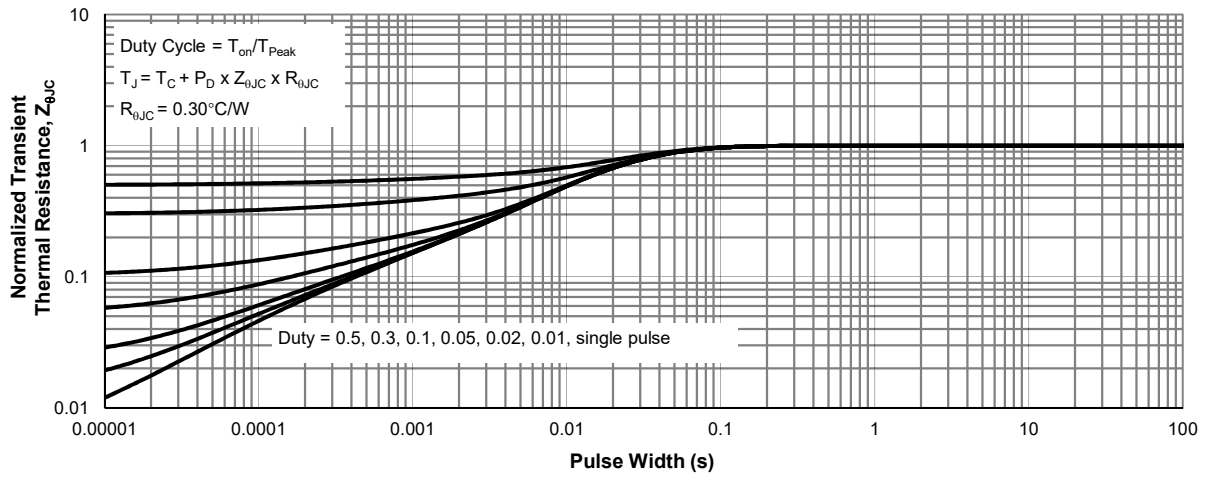
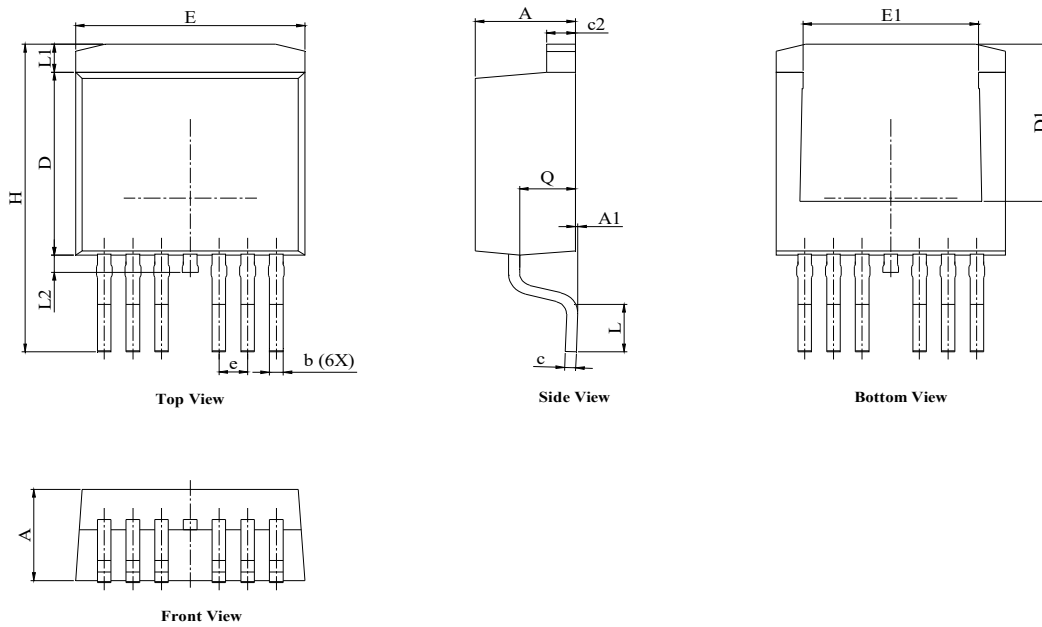
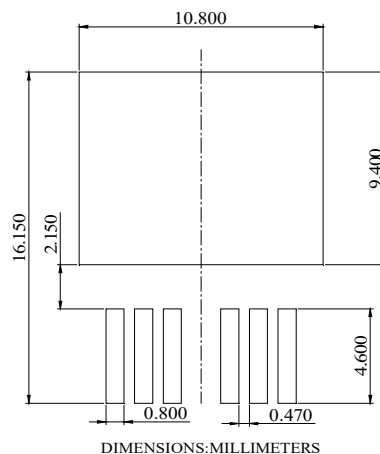


Figure 13: Normalized Maximum Transient Thermal Impedance

TO-263-7L Package Information
Package Outline


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	7.65 REF.		
E	9.96	10.16	10.36
E1	6.80	7.80	8.00
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.80
L1		1.36 REF.	
L2		1.20 REF.	
L3		0.25 BSC	
Q	2.30	2.48	2.70

Recommended Soldering Footprint


DIMENSIONS: MILLIMETERS

单击下面可查看定价，库存，交付和生命周期等信息

[>>JW\(捷捷微\)](#)